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Cancel claim 20.

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21. (Amended) The method of claim 30, wherein the using of said first material as a mask comprises providing at least one first region from which said opaque material is removed, and the removing of said first material comprises providing at least one second region from which said first material is removed, said first and second regions having different phase shift characteristics with respect to light transmitted therethrough.

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Cancel claims 28 and 29.

30. (Amended) A method of forming a mask, comprising:
forming an opaque layer over a substrate, said opaque layer having at least one opening therein filled with a first material, said first material defining areas of said substrate which are to be removed, said forming comprising:

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depositing a first resist material on said opaque layer;
removing a portion of said first resist material, leaving said opening;
etching an uncovered portion of said opaque layer underlying the removed portion of said first resist material, thereby deepening said opening a first time; and
removing the remainder of said first resist material;

etching the substrate defined by said deepened opening, thereby deepening said opening a second time;

using said first material as a mask to remove said areas of said substrate, wherein the using of said first material as a mask comprises:

providing said first material within said twice deepened opening and over said opaque layer;

directing a first exposure through said substrate to expose a portion of said first material;

hardening the exposed portion of said first material;

directing a second exposure at said first material to remove any unhardened portions of said first material;

providing a second material over said opaque layer and said hardened portion of said first material;

performing a lithographic step on a portion of said second material overlying and bounded by said first material to expose and remove said portion of said second material; and

etching said opaque layer underlying said exposed and removed portion of said second material; and

removing said first material.

33. (Amended) The method of claim 30, wherein the using of said first material as a mask comprises:

providing said first material within said deepened opening and over said opaque layer;

directing a first exposure through said substrate to expose a portion of said first material;

baking said first material to harden the exposed portion of said first material;

directing a second exposure at said first material to remove any unhardened portions of said first material;

providing a second material over said opaque layer and said hardened portion of said first material;

performing a lithographic step on a portion of said second material overlying and bounded by said first material to expose and remove said portion of said second material; and

etching said opaque layer underlying said exposed and removed portion of said second material.

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Cancel claim 36.

37. (Amended) A mask comprising at least one printable area which is self-aligned with respect to an adjacent phase shift area, said mask including:

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a layer located over said substrate, the adjacent phase shift area being formed in said layer; and

an opaque layer over said layer.

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42. (Amended) The mask of claim 37, wherein said printable area is located within said substrate and said adjacent phase shift area is located in said opaque layer.

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Cancel claim 44.